TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM5N15FE

High Speed Switching Applications Analog Switch Applications

· Small package

• Low ON resistance : $R_{on} = 4.0 \Omega (max) (@V_{GS} = 4 V)$

: $R_{on} = 7.0 \Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$

Absolute Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

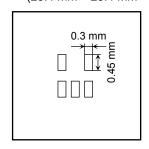
Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V_{DS}	30	V	
Gate-Source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	100	mA	
	Pulse	I _{DP}	200		
Drain power dissipation (Ta = 25°C)		P _D (Note 1)	150	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note:

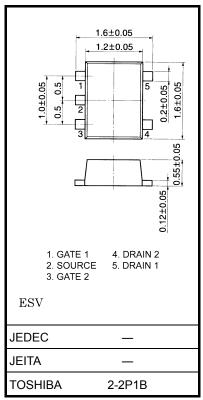
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating, mounted on FR4 board (25.4 mm \times 25.4 mm \times 1.6 t, Cu Pad: 0.135 mm $^2 \times$ 5)

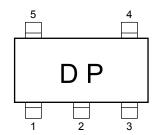


Unit: mm

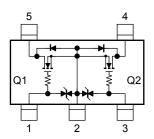


Weight: 0.003 g (typ.)

Marking



Equivalent Circuit (top view)



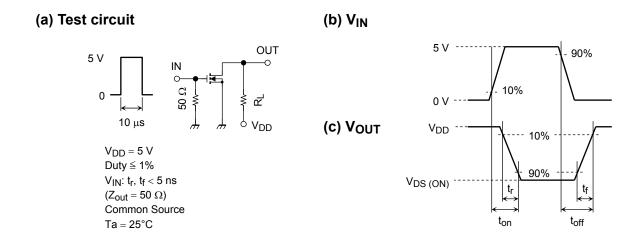
Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristic		Symbol	Test Condition	Min	Тур	Max	Unit	
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	_	_	±1	μА	
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	30	_	_	V	
Drain cut-off current		I _{DSS}	V _{DS} = 30 V, V _{GS} = 0	_	_	1	μА	
Gate threshold voltage	;	V_{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.8	_	1.5	V	
Forward transfer admittance		Y _{fs}	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$	25	_	_	mS	
Drain-Source ON resistance		R _{DS} (ON)	$I_D = 10$ mA, $V_{GS} = 4$ V	_	2.2	4.0	Ω	
			I _D = 10 mA, V _{GS} = 2.5 V	_	4.0	7.0	22	
Input capacitance		C _{iss}		_	7.8	_	pF	
Reverse transfer capacitance		C _{rss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.6	_	pF	
Output capacitance		C _{oss}		_	8.8	_	pF	
Switching time	Turn-on time	t _{on}	$V_{DD} = 5 \text{ V}, I_D = 10 \text{ mA},$	_	50	_	ns	
	Turn-off time	t _{off}	V _{GS} = 0~5 V	_	180	_		

Switching Time Test Circuit

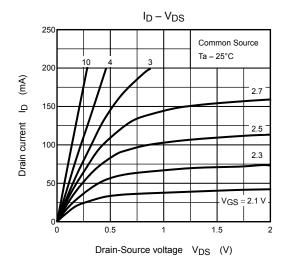


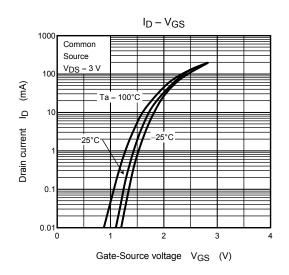
Precaution

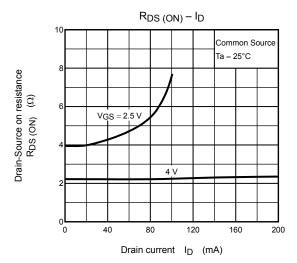
 V_{th} can be expressed as voltage between gate and source when low operating current value is I_D = 100 μA for this product. For normal switching operation, V_{GS} (on) requires higher voltage than V_{th} and V_{GS} (off) requires lower voltage than V_{th} . (Relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on))

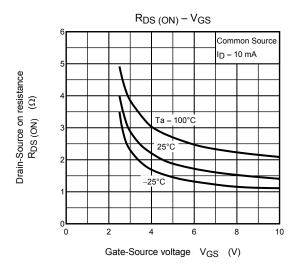
Please take this into consideration for using the device.

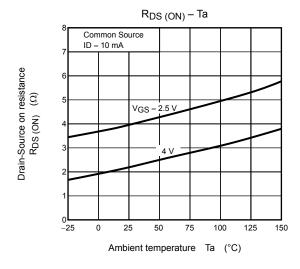
(Q1, Q2 common)

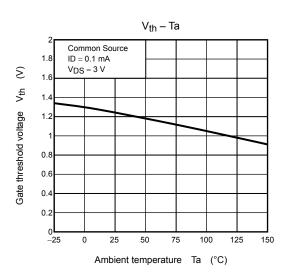




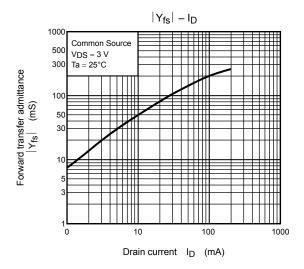


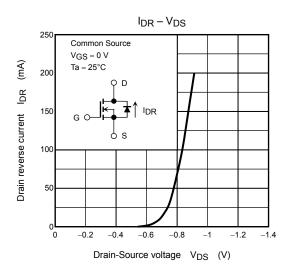


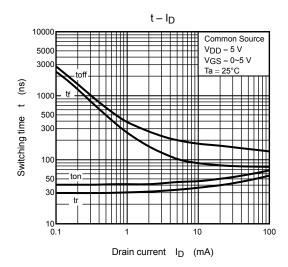


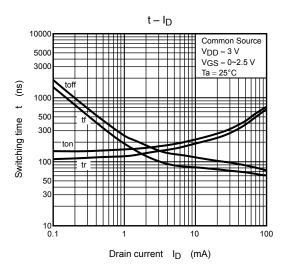


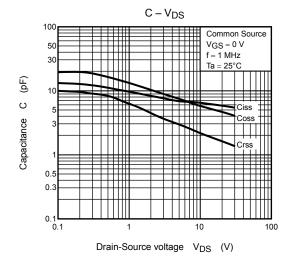
(Q1, Q2 common)

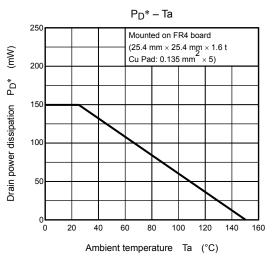












*: Total rating

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20070701-EN GENERAL

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